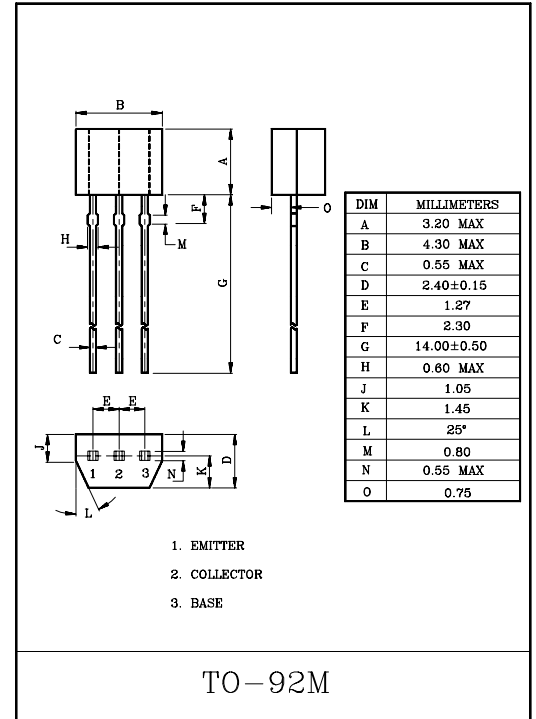
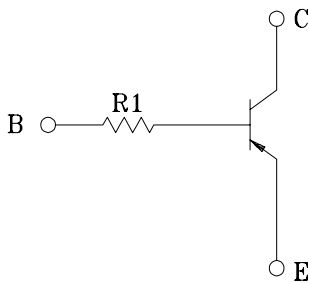


SWITCHING APPLICATION.
INTERFACE CIRCUIT AND DRIVER CIRCUIT APPLICATION.

FEATURES

- With Built-in Bias Resistors.
- Simplify Circuit Design.
- Reduce a Quantity of Parts and Manufacturing Process.

EQUIVALENT CIRCUIT



MAXIMUM RATINGS (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-100	mA
Collector Power Dissipation	P_C	400	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55~150	℃

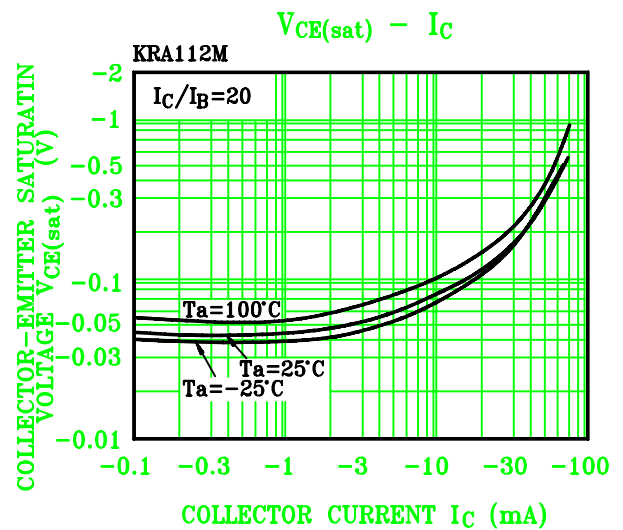
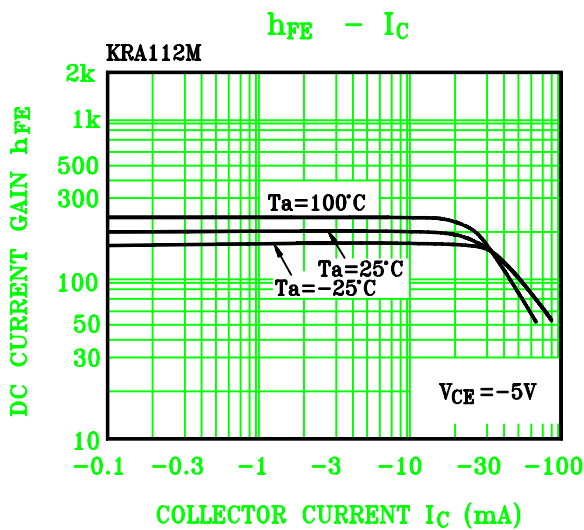
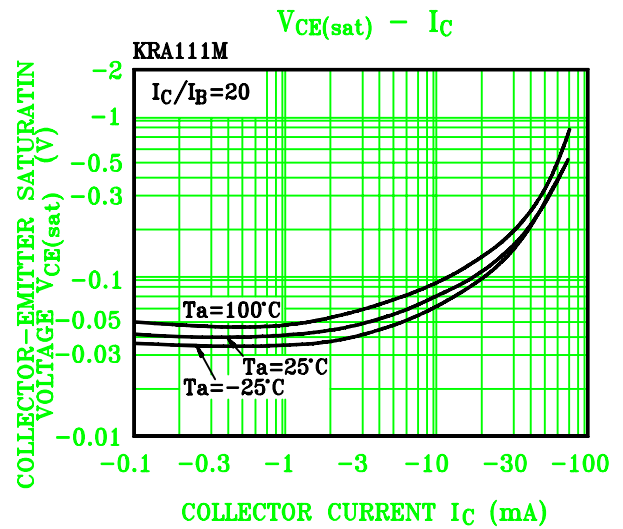
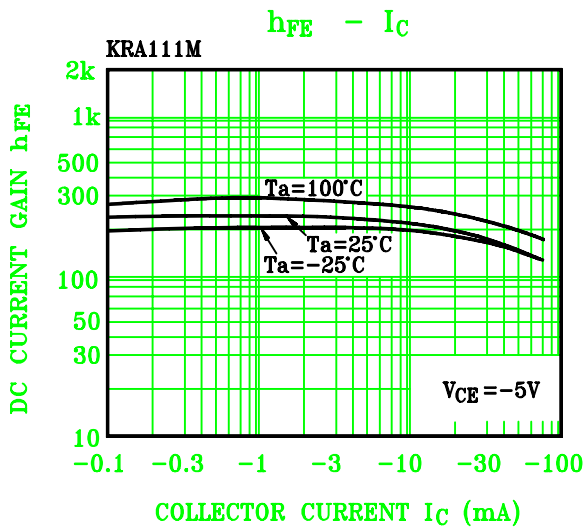
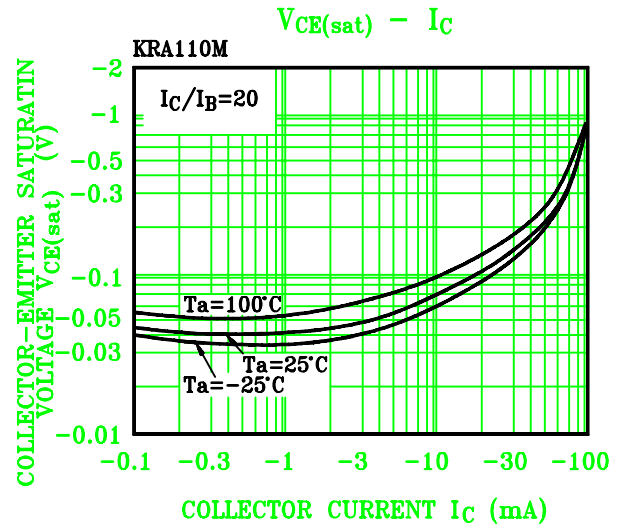
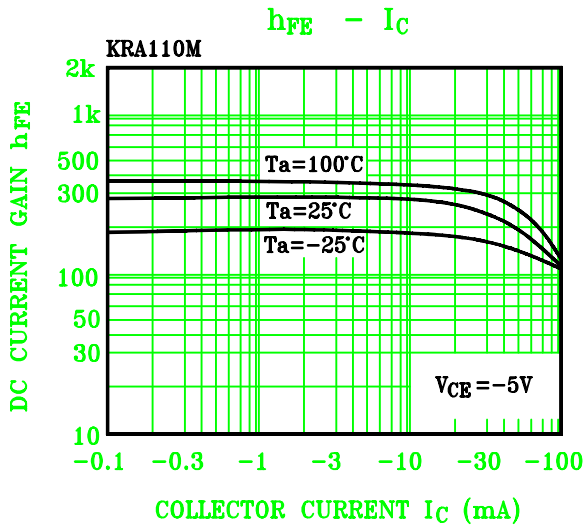
KRA110M~KRA114M

ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	$V_{CB}=-50V, I_E=0$	-	-	-100	nA
Emitter Cut-off Current		I_{EBO}	$V_{EB}=-5V, I_C=0$	-	-	-100	nA
DC Current Gain		h_{FE}	$V_{CE}=-5V, I_C=-1mA$	120	-	-	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C=-10mA, I_B=-0.5mA$	-	-0.1	-0.3	V
Transition Frequency		$f_T *$	$V_{CE}=-10V, I_C=-5mA$	-	250	-	MHz
Input Resistor		KRA110M		-	4.7	-	k Ω
		KRA111M		-	10	-	
		KRA112M		-	100	-	
		KRA113M		-	22	-	
		KRA114M		-	47	-	
Switching Time	Rise Time	KRA110M	t_r	-	0.2	-	μS
		KRA111M		-	0.065	-	
		KRA112M		-	0.4	-	
		KRA113M		-	0.1	-	
		KRA114M		-	0.15	-	
	Storage Time	KRA110M	t_{stg}	-	2.0	-	
		KRA111M		-	1.7	-	
		KRA112M		-	3.0	-	
		KRA113M		-	2.0	-	
		KRA114M		-	1.5	-	
	Fall Time	KRA110M	t_f	-	0.3	-	
		KRA111M		-	0.3	-	
		KRA112M		-	1.7	-	
		KRA113M		-	0.8	-	
		KRA114M		-	1.5	-	

Note; * Characteristic of Tranistor Only

KRA110M~KRA114M



KRA110M~KRA114M

